

Fig. 1 (Prior Art)

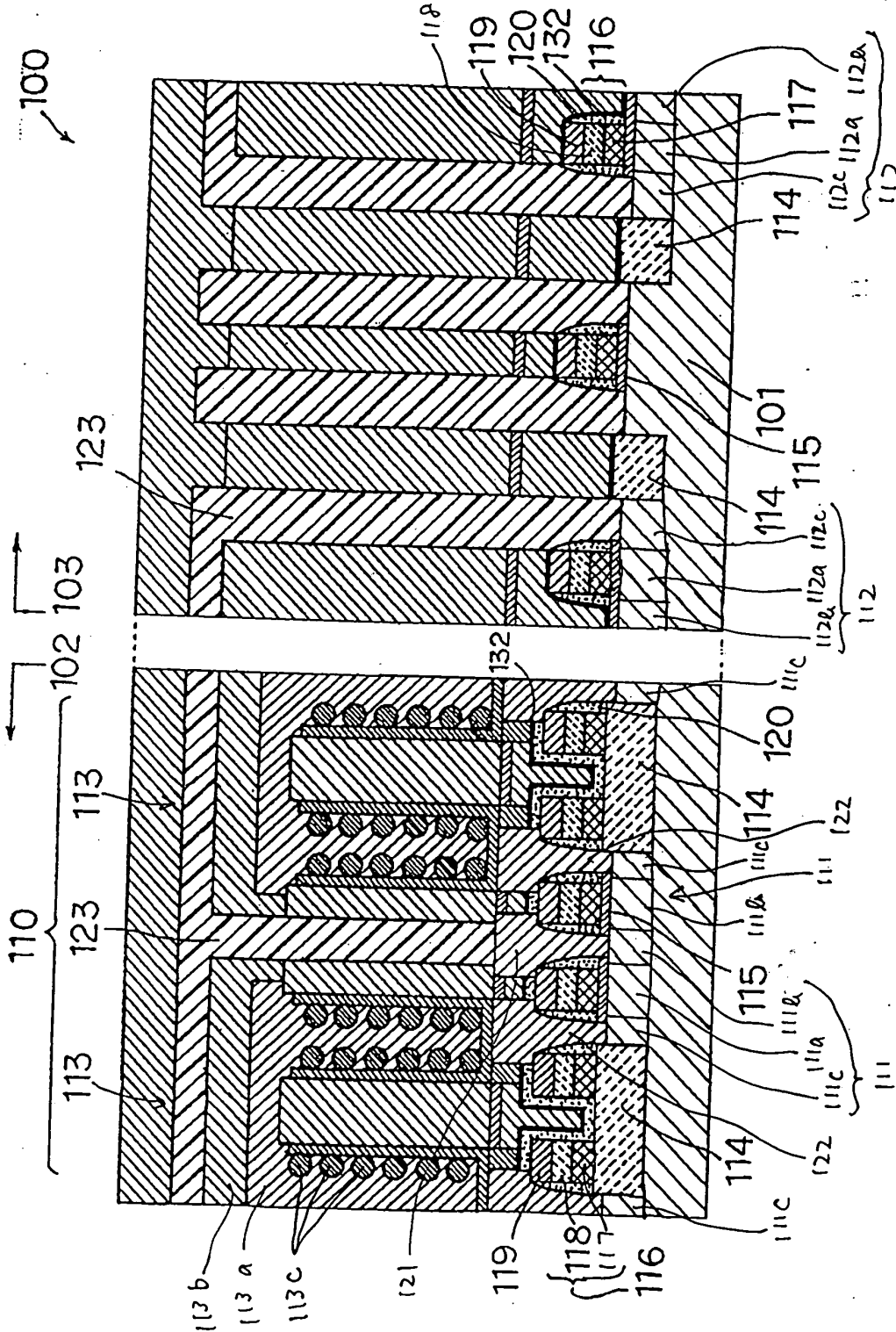


FIG. 2 SEMICONDUCTOR DEVICE WITH HIGH-
AND LOW-DENSITY REGIONS OF
TRANSISTOR ELEMENTS ON SINGLE
SEMICONDUCTOR SUBSTRATE, AND
METHOD OF MANUFACTURING SUCH
SEMICONDUCTOR DEVICE

Inventor(s): Toshiyuki HIROTA, et al.

DOCKET NO.: 040373/0300

Fig. 2 (Prior Art)

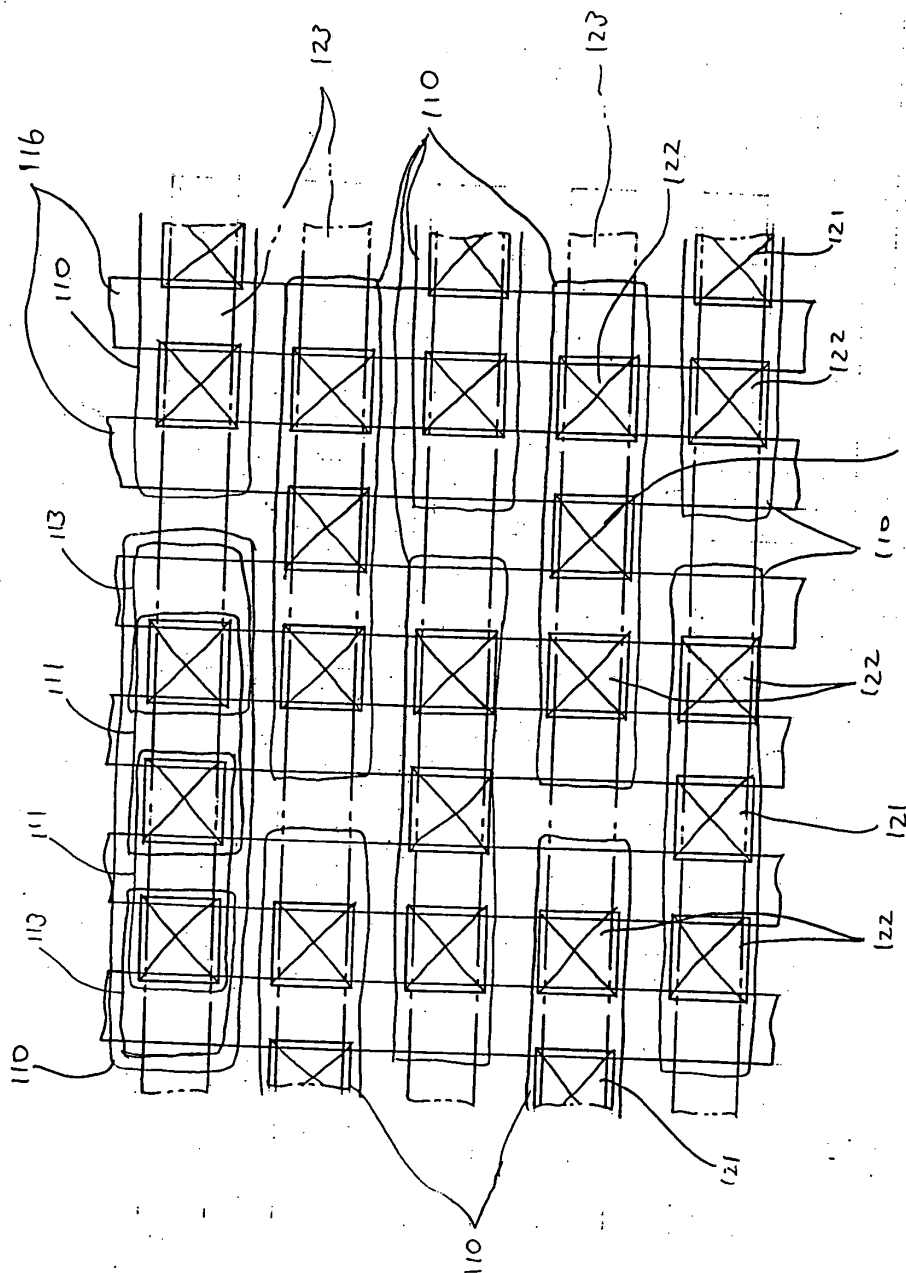
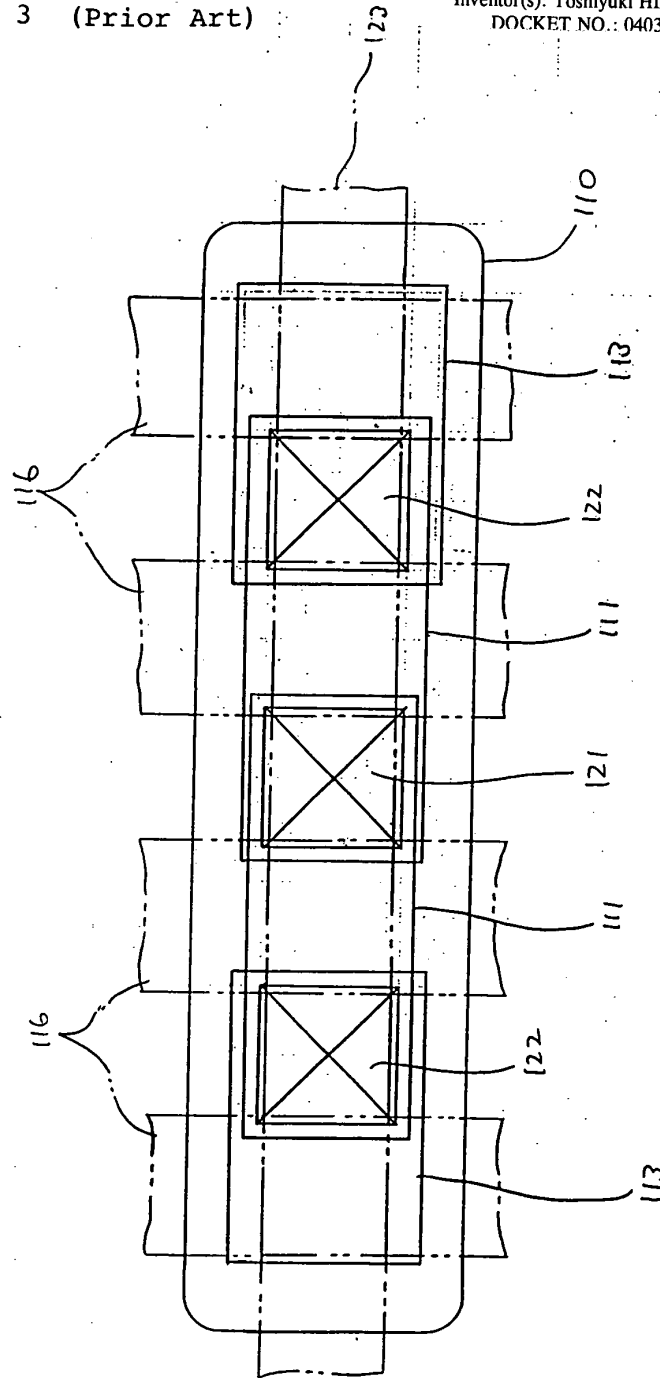


Fig. 3 (Prior Art)

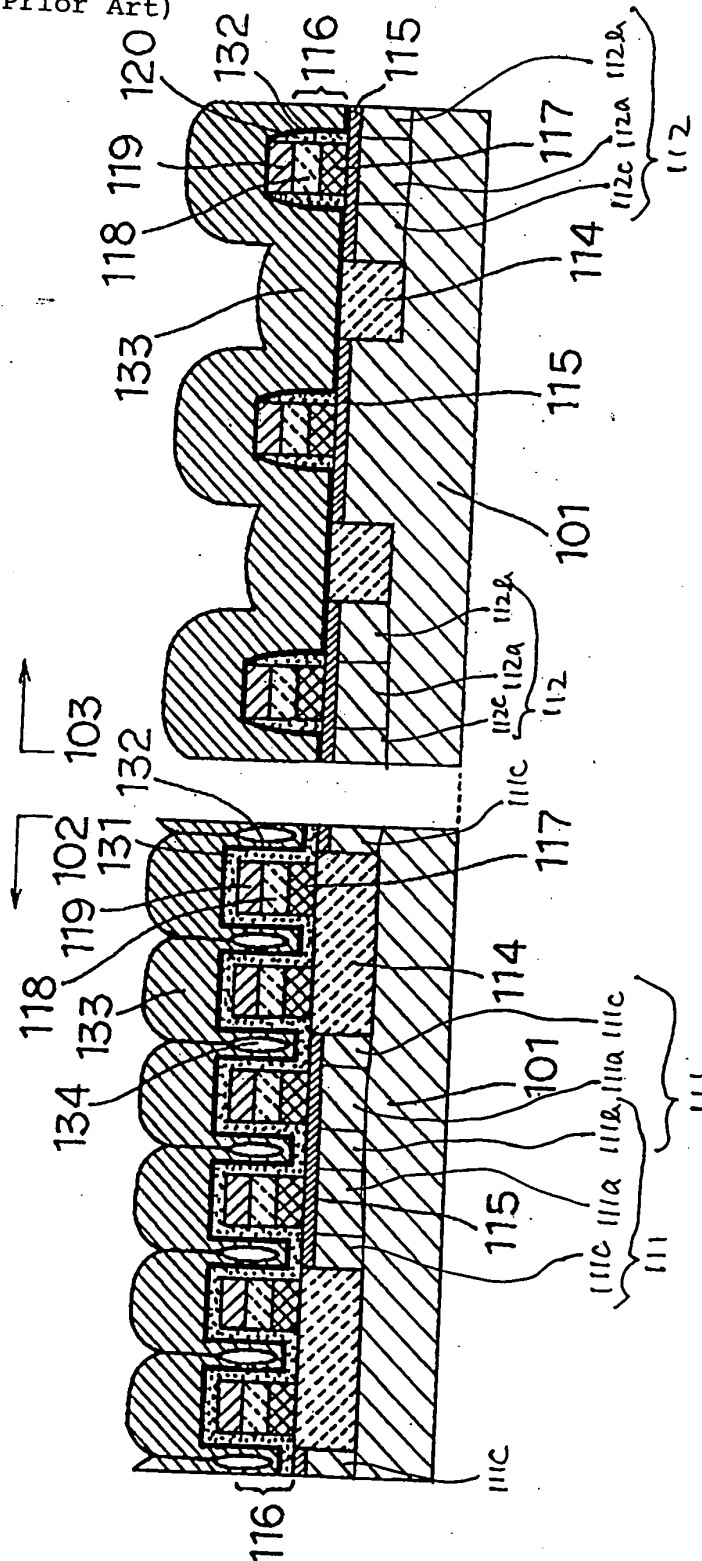


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TITLE: SEMICONDUCTOR DEVICE WITH HIGH
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DOCKET NO.: 040373/0300

Fig. 4 (Prior Art)



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Fig. 5 (Prior Art)

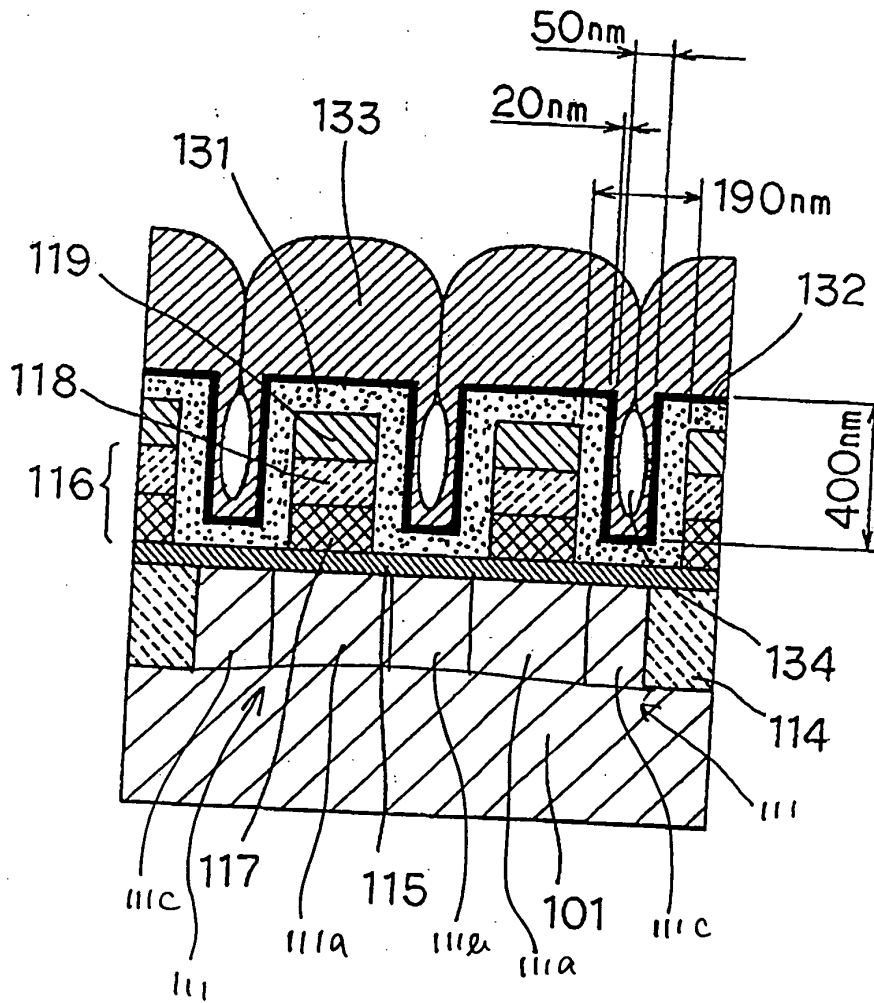


Fig. 6 (Prior Art)

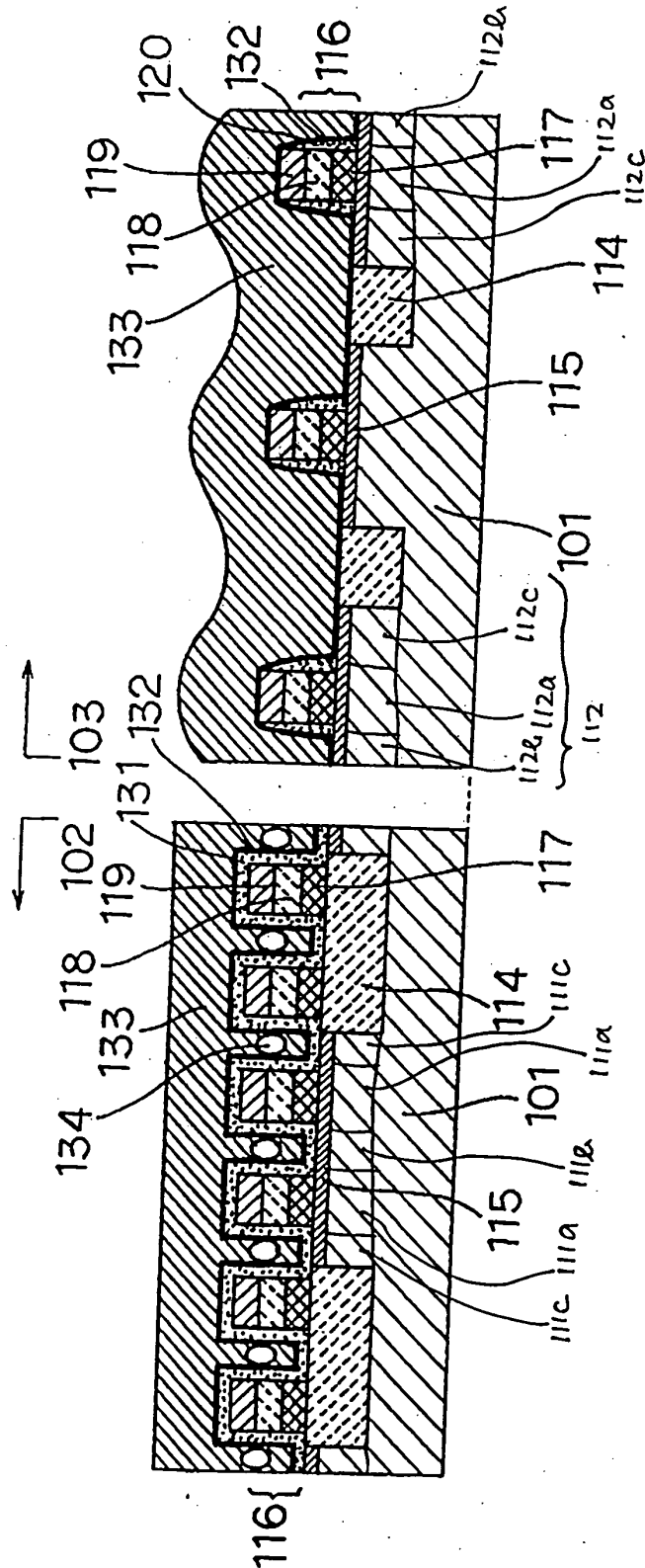
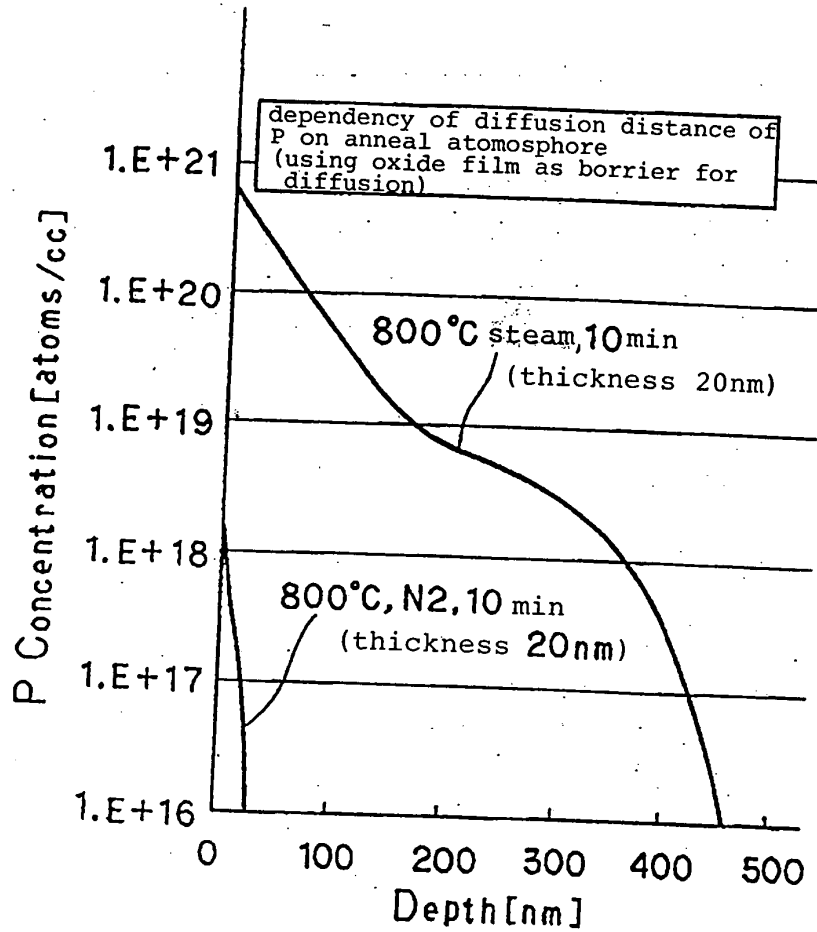


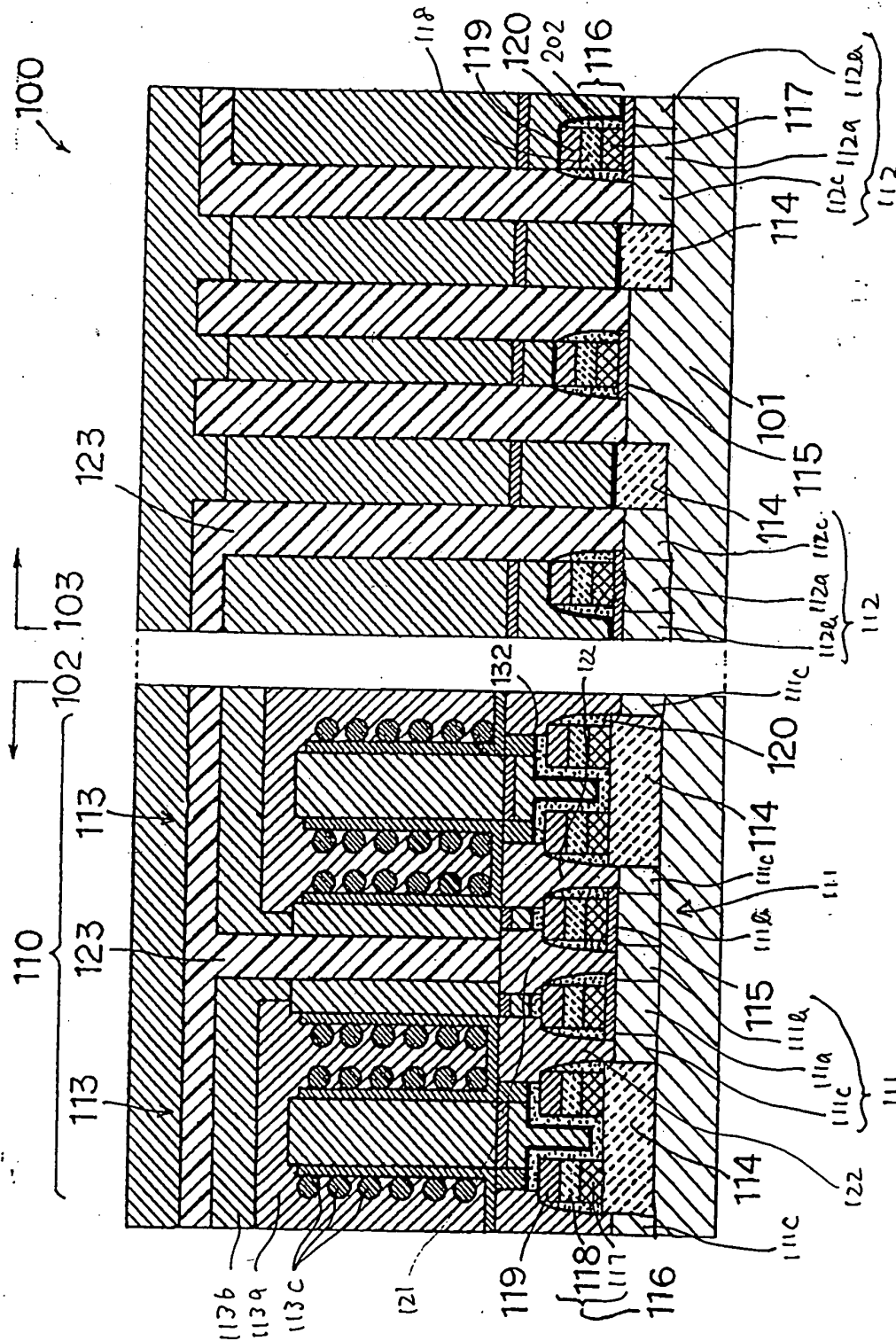
Fig. 7 (Prior Art)



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Fig. 8

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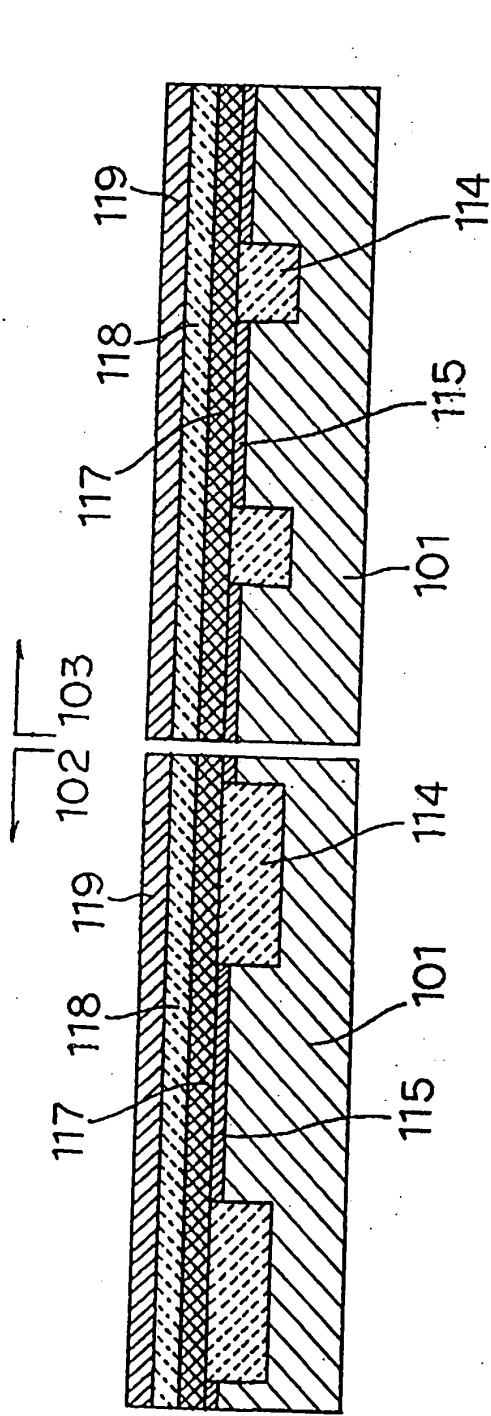


Fig. 9A

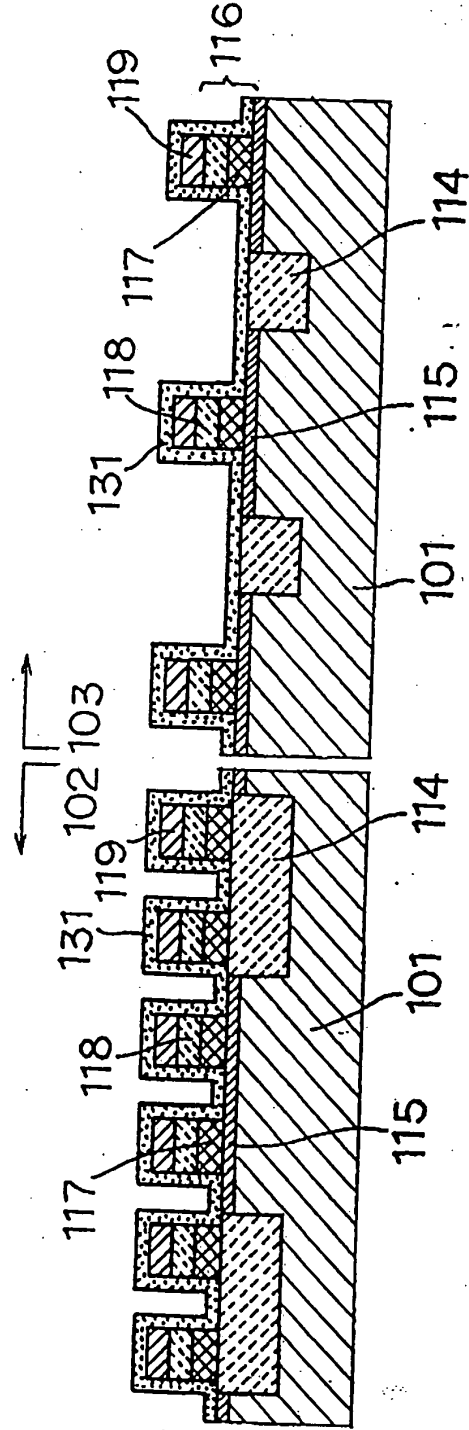


Fig. 9B



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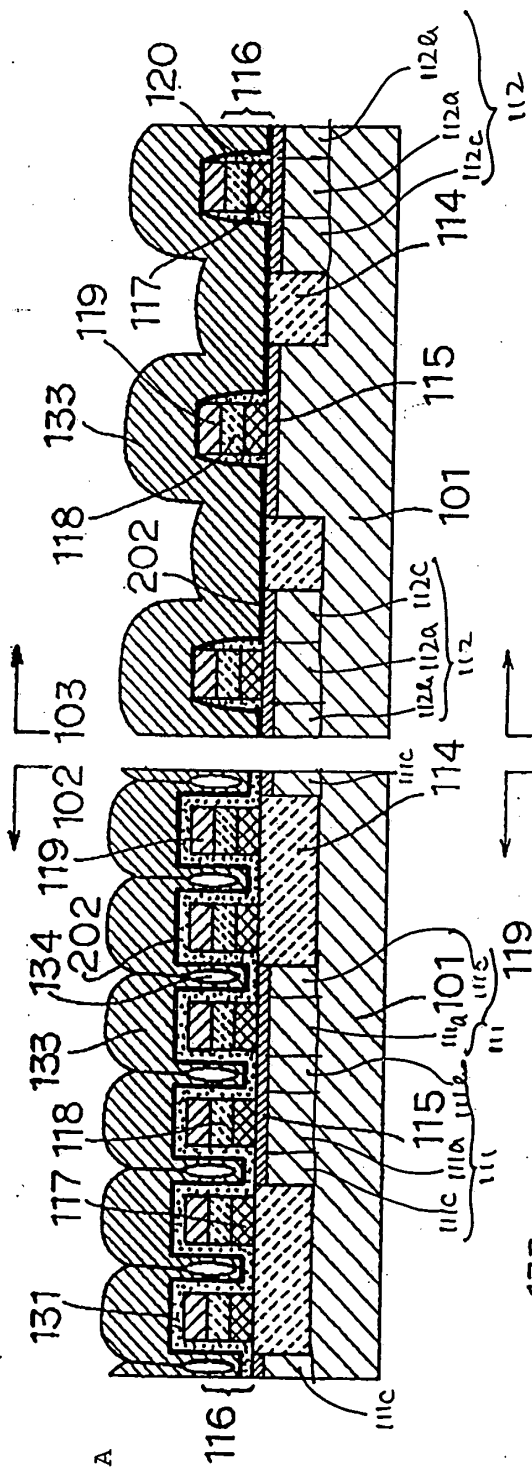


Fig. 11A

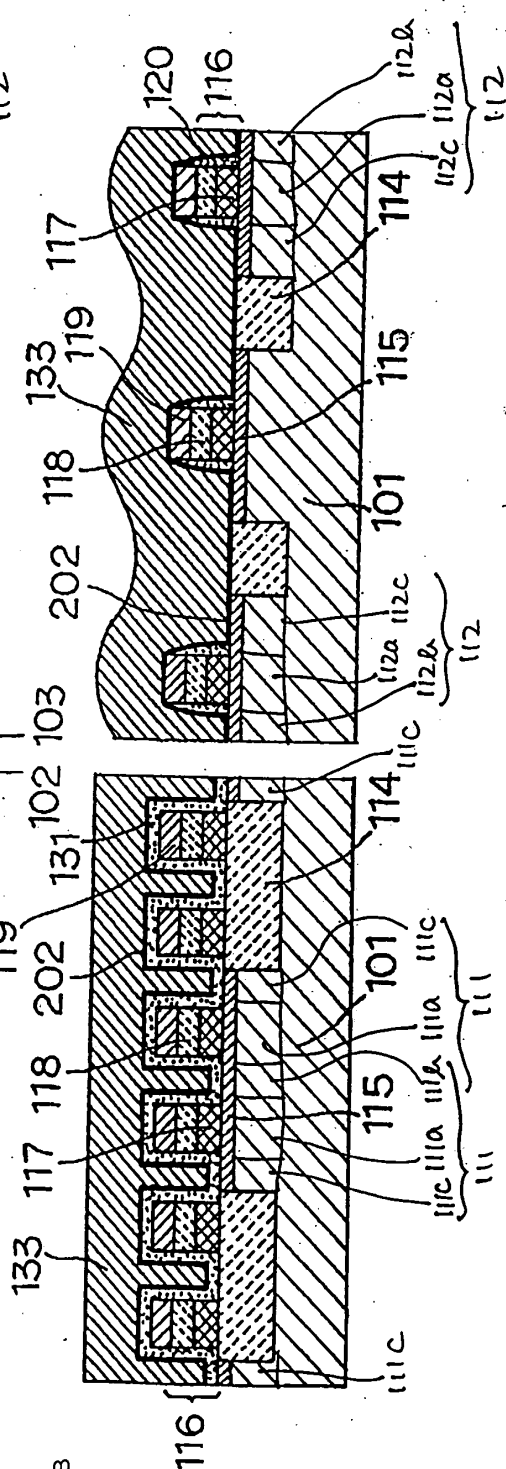


Fig. 11B

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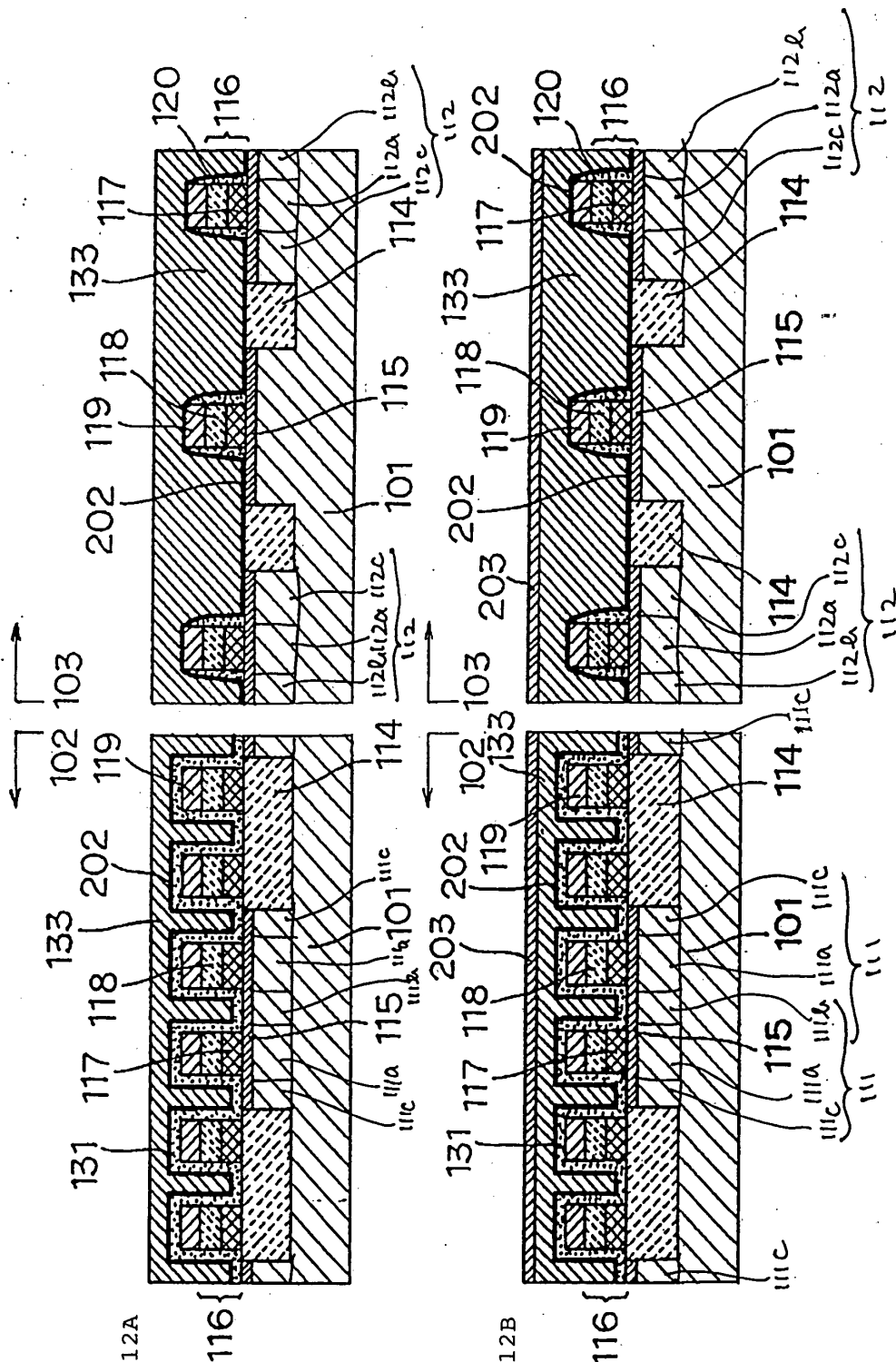


Fig. 12A

Fig. 12B

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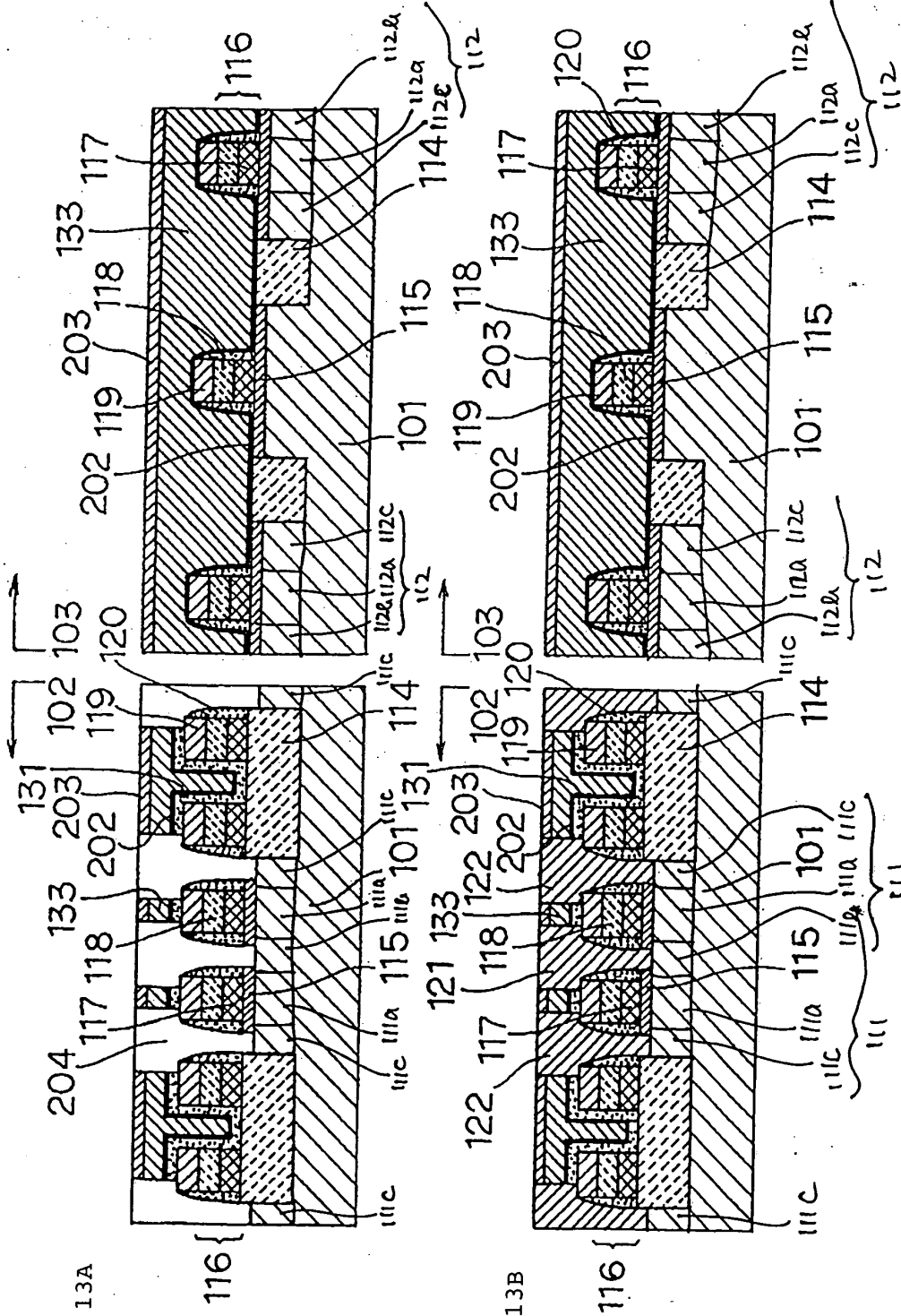


Fig. 13A

Fig. 13B

Fig. 14

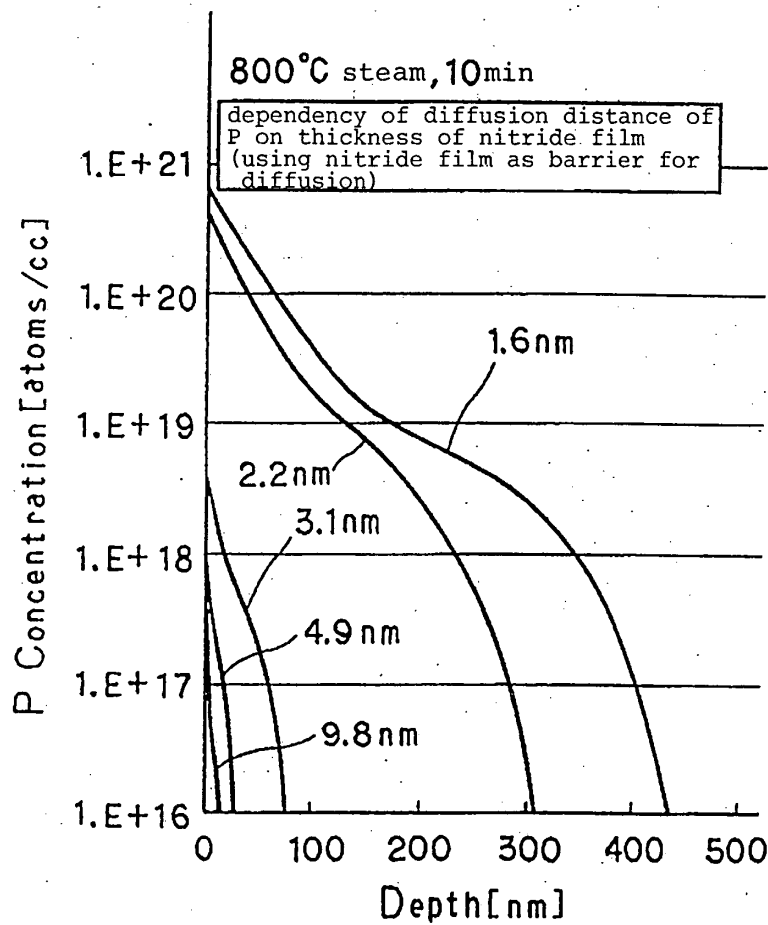


Fig. 15

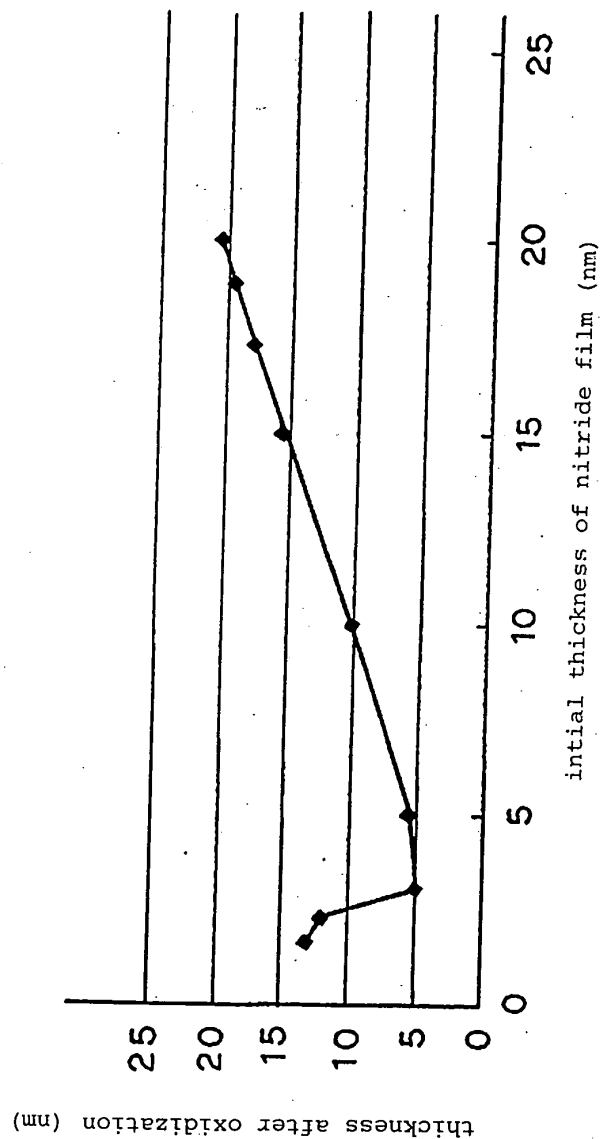


Fig. 16

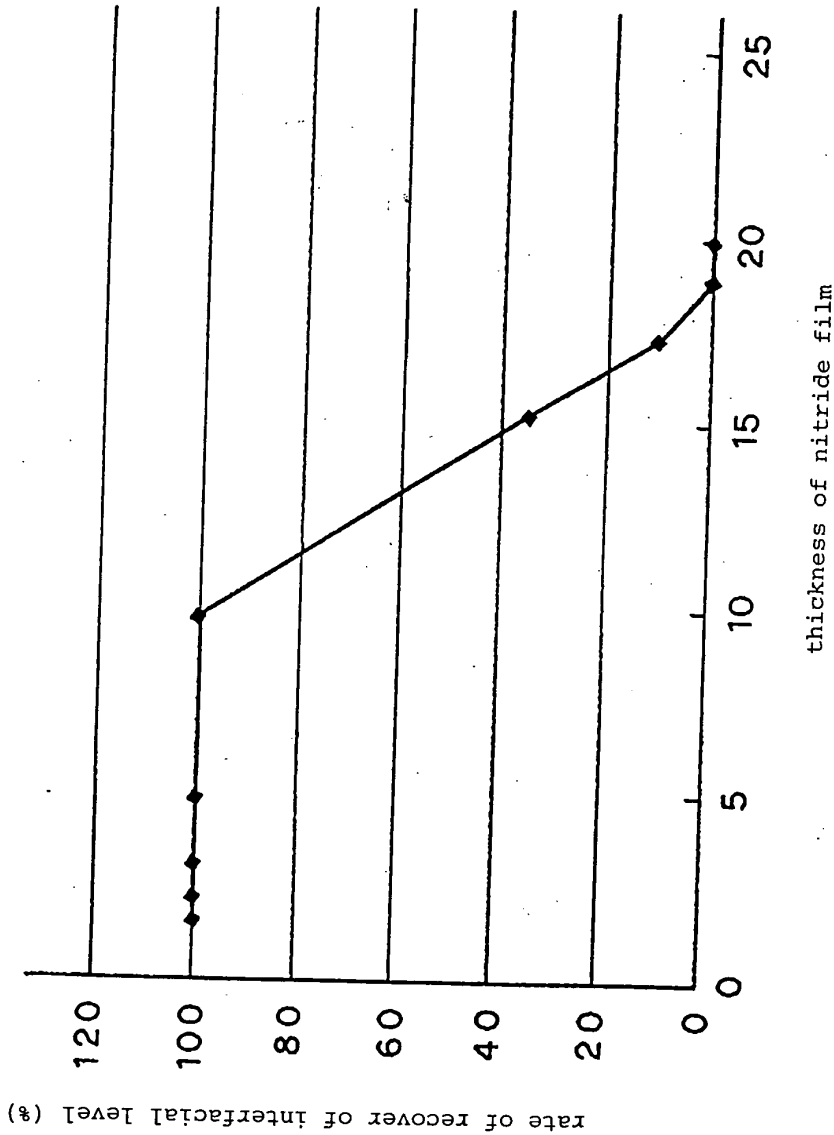
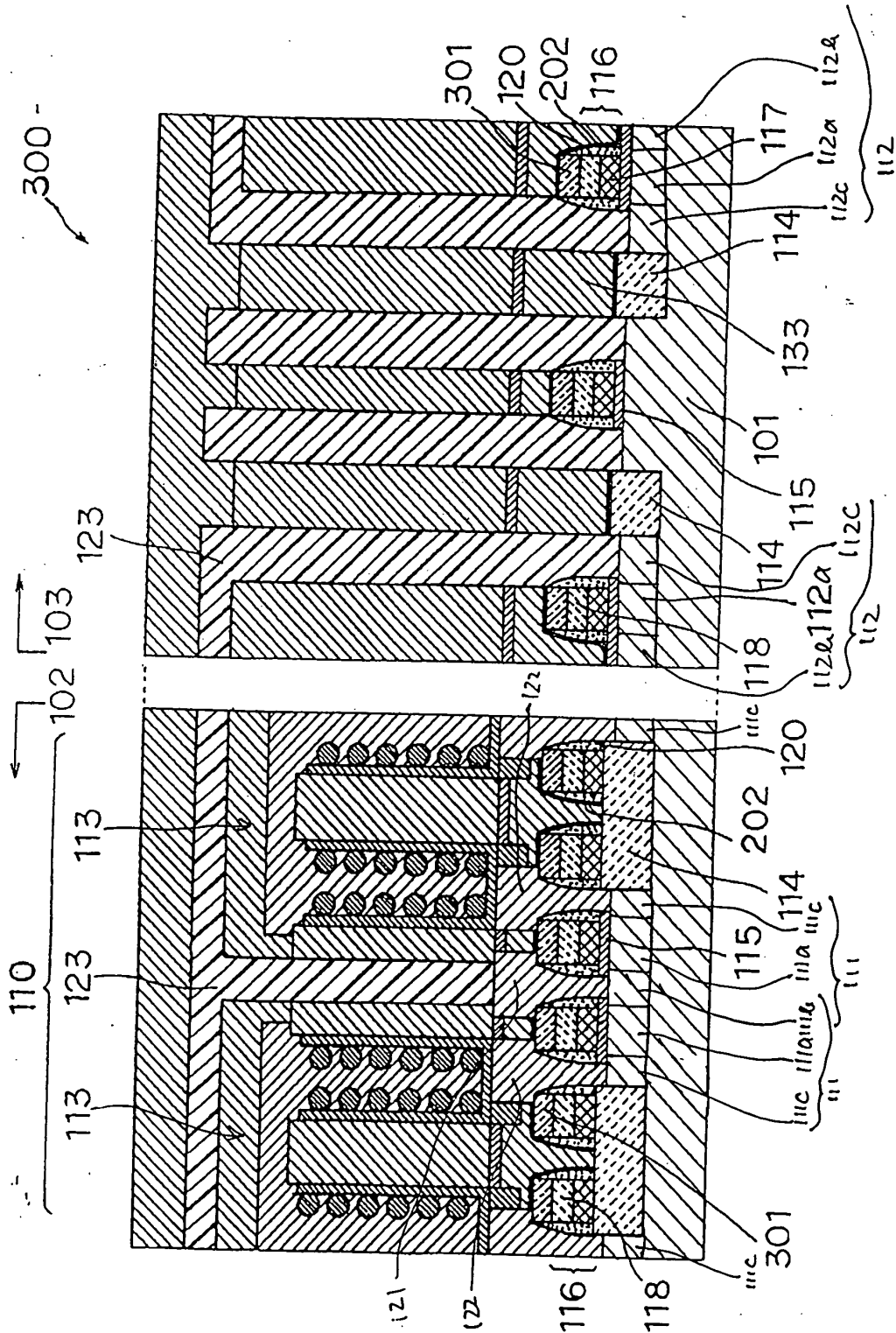


Fig. 17



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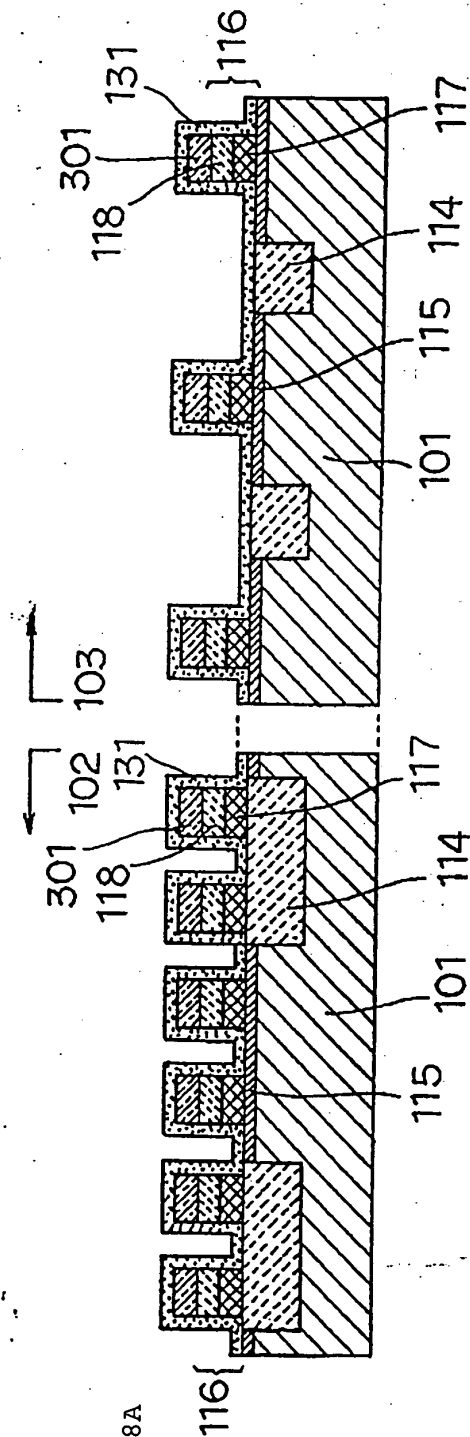


Fig. 18A

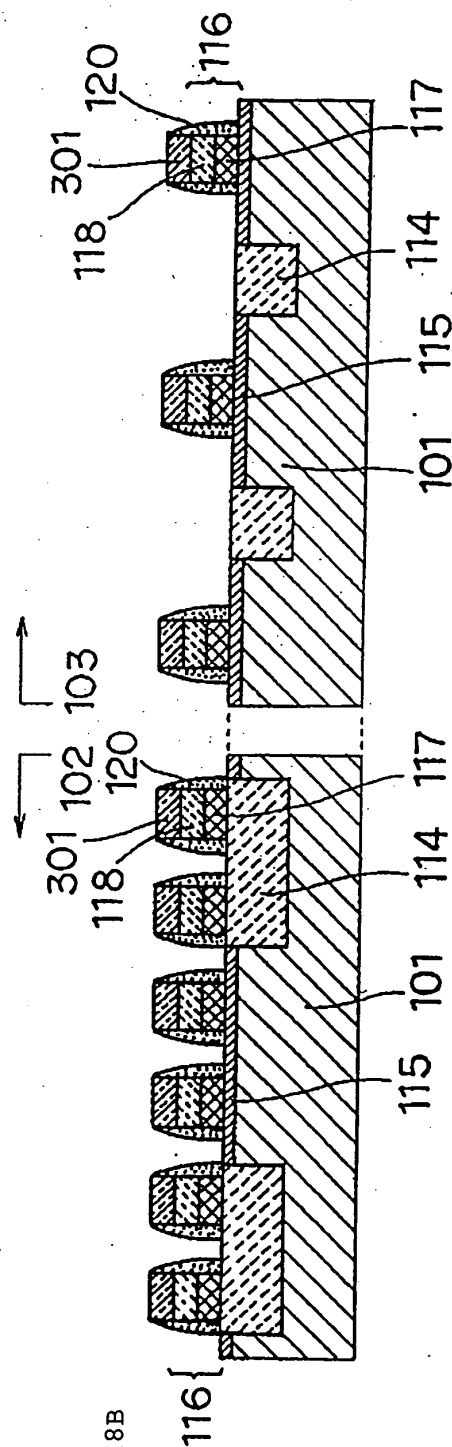


Fig. 18B

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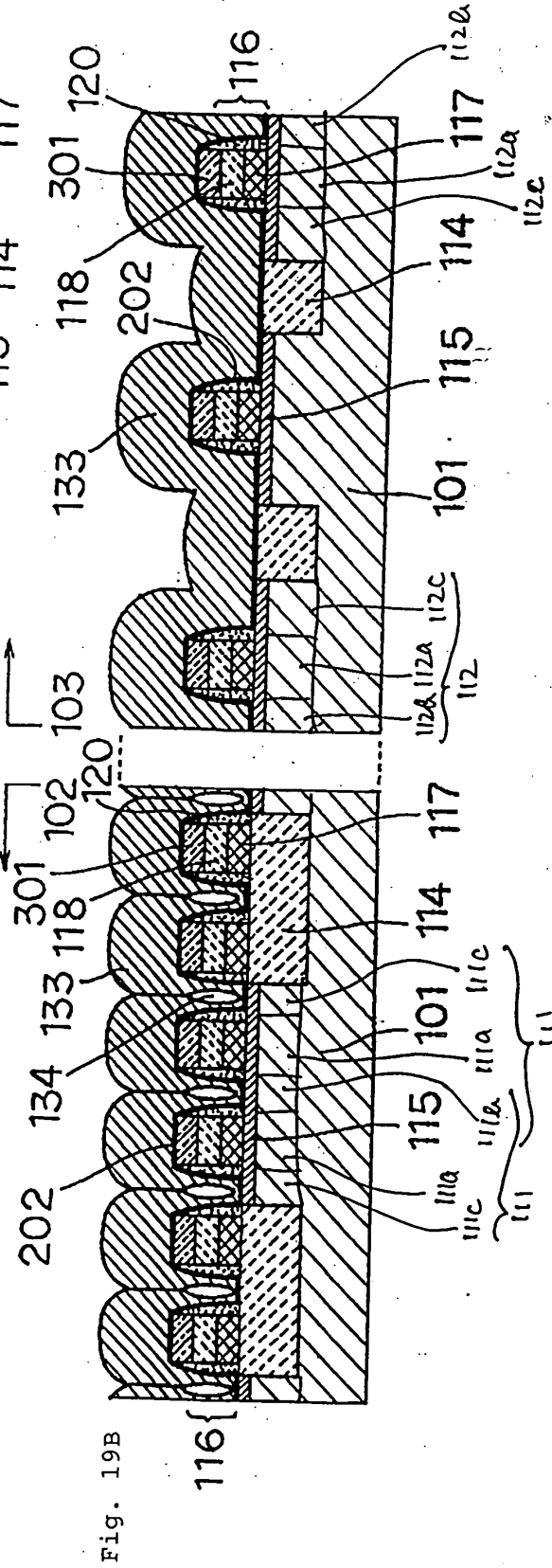
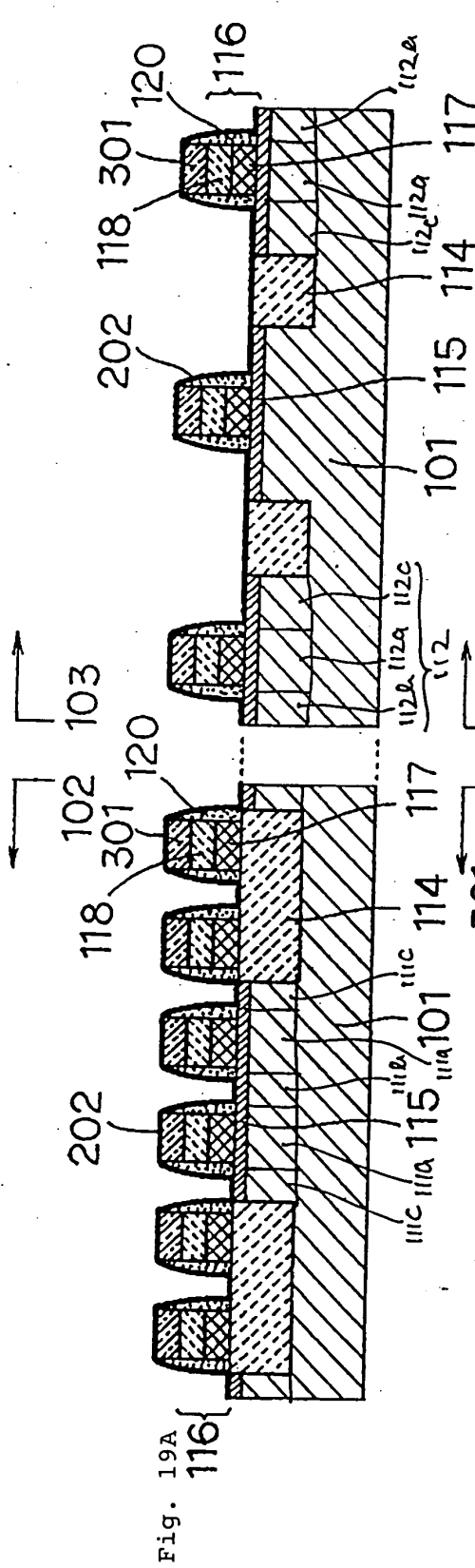




Fig. 21

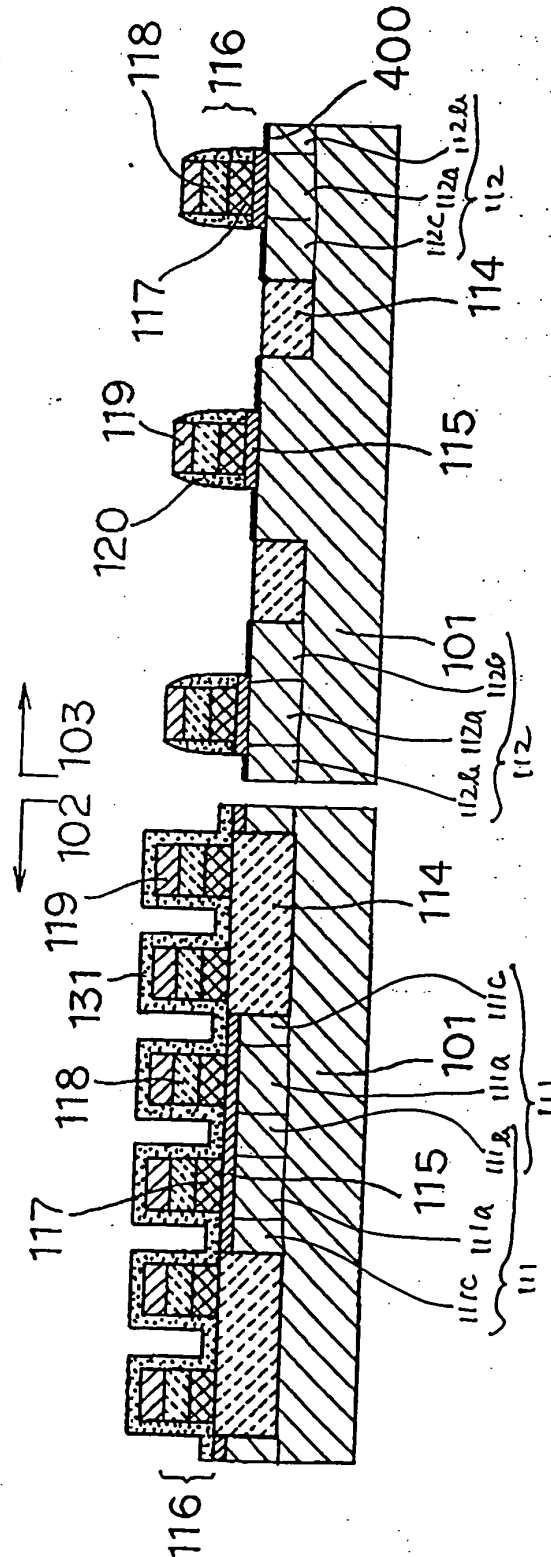
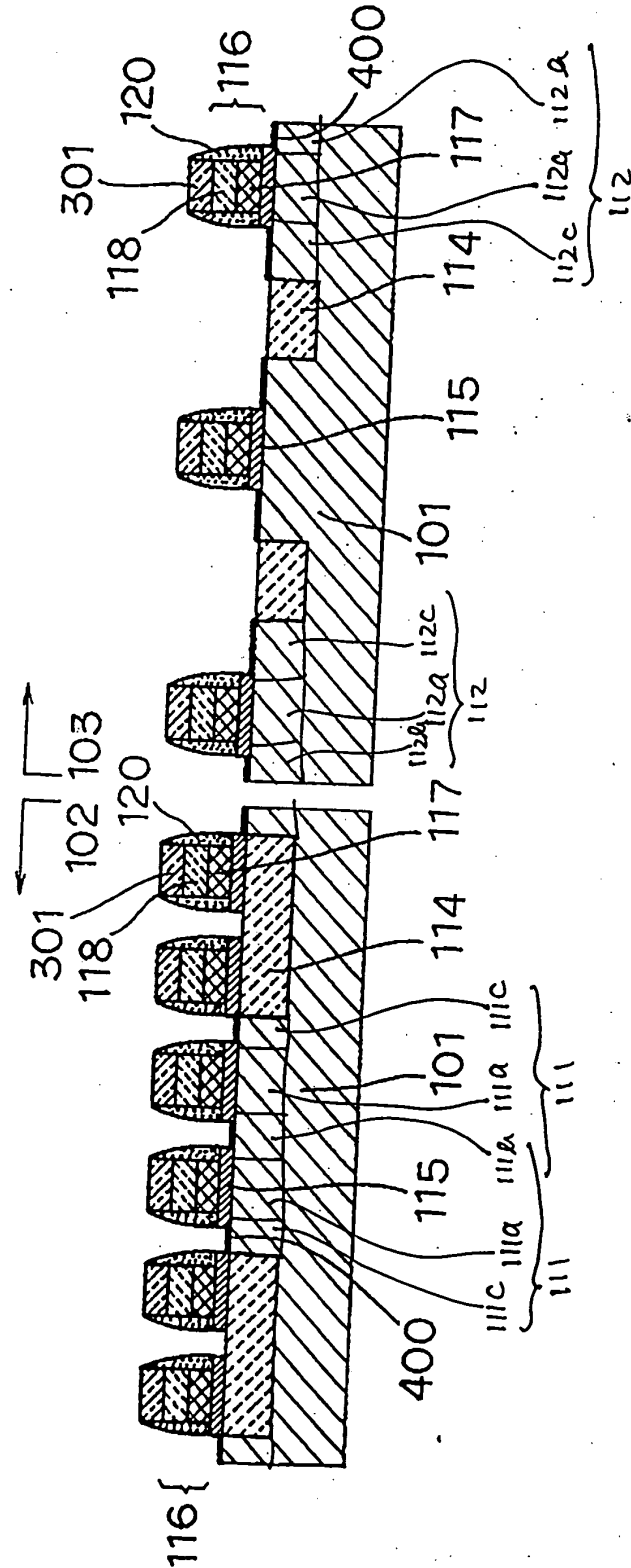


Fig. 22



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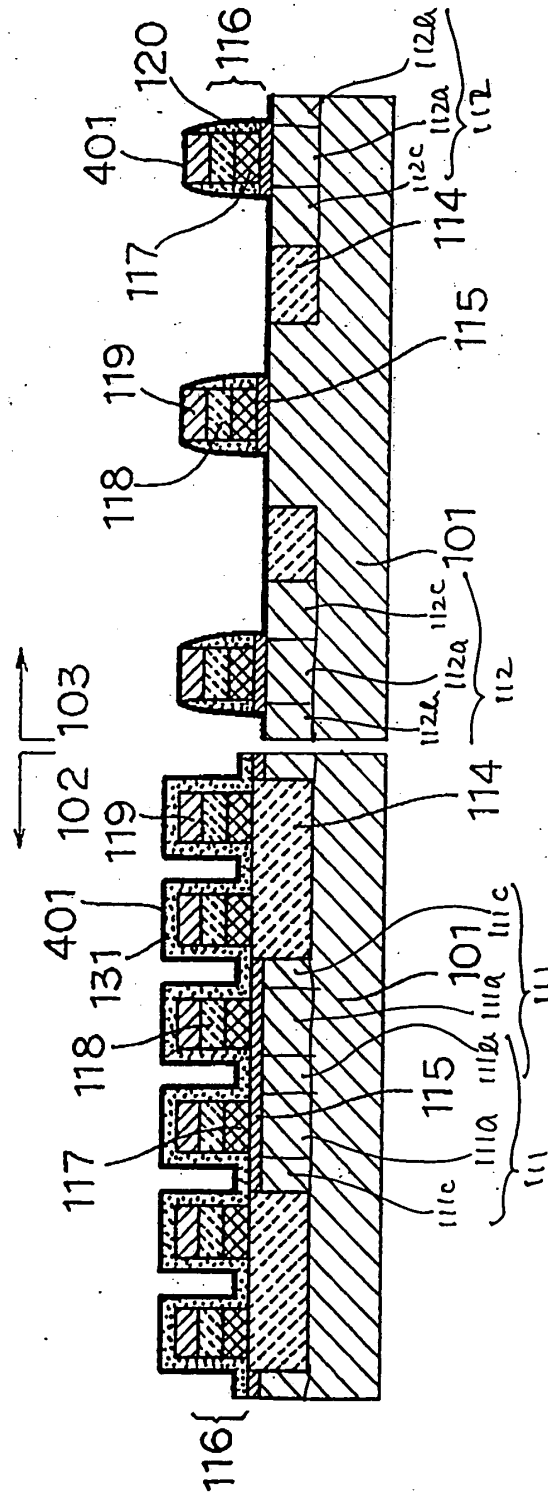
[illegible]

Fig. 24

